

Notice of References Cited	Application/Control No. 10/598,744	Applicant(s)/Patent Under Reexamination PAWLAK, BARTLOMIEJ JAN	
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U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-4,584,026 A	04-1986	Wu et al.	438/528
*	B	US-5,407,838 A	04-1995	Ohnishi et al.	438/369
*	C	US-5,969,398 A	10-1999	Murakami, Takashi	257/412
*	D	US-6,037,640 A	03-2000	Lee, Kam Leung	257/408
*	E	US-6,069,062 A	05-2000	Downey, Daniel F.	438/528
*	F	US-6,087,209 A	07-2000	Yeap et al.	438/197
*	G	US-6,261,889 B1	07-2001	Ono, Atsuki	438/232
*	H	US-2001/0041432 A1	11-2001	Lee, Kam Leung	438/530
*	I	US-2003/0109119 A1	06-2003	Chakravarthi et al.	438/563
*	J	US-2003/0207542 A1	11-2003	Chidambaram et al.	438/305
*	K	US-2004/0173843 A1	09-2004	Noda, Taiji	257/327
*	L	US-2004/0235280 A1	11-2004	Keys et al.	438/528
*	M	US-2005/0158956 A1	07-2005	Poon et al.	438/282

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

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	X	

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	Examiner George Fourson		Art Unit 2823	Page 2 of 2

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2006/0205192 A1	09-2006	Walther et al.	438/513
*	B	US-2006/0223264 A1	10-2006	Park et al.	438/266
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

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	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Ya, L., "The Effect of Fluorine on the Redistribution of Boron in Ion-implanted Silicon", J. Appl. Phys.74(10), 15 NOV 1993, pp.6020-6022
	V	Huang, T.H., "Influence of Fluorine Preamorphization on the Diffusion and Activation of Low-Energy Implanted Boron During Rapid Thermal Annealing", Appl. Phys. Lett. 65(14), 3 OCT 1994, pp.1829-1831
	W	Saito, S., "Defect Reduction by MeV Ion Implantation for Shallow Junction Formation", Appl. Phys. Lett. 63(2), 12 July 1993, pp.197-199.
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.